

2N5460, 2N5461, 2N5462

P-Channel Silicon Junction Field-Effect Transistor

- Audio Amplifiers
- General Purpose Amplifiers

Absolute maximum ratings at 25 °C

Reverse Gate Source & Reverse Gate Drain Voltage	40 V
Continuous Forward Gate Current	- 10 mA
Continuous Device Power Dissipation	310 mW
Power Derating	2.8 mW/°C

At 25°C free air temperature:
Static Electrical Characteristics

		2N5460		2N5461		2N5462		Process PJ32	
		Min	Max	Min	Max	Min	Max	Unit	Test Conditions
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	40		40		40		V	$I_G = 10\mu A, V_{DS} = 0V$
Gate Reverse Current	I_{GSS}		5		5		5	nA	$V_{GS} = 20V, V_{DS} = 0V$
			1		1		1	μA	$V_{GS} = 20V, V_{DS} = 0V$
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	0.75	6	1	7.5	1.8	9	V	$V_{DS} = -15V, I_D = -1\mu A$
Gate Source Voltage	V_{GS}	0.8	4.5					V	$V_{DS} = -15V, I_D = -100\mu A$
				0.8	4.5			V	$V_{DS} = -15V, I_D = -200\mu A$
						1.5	6	V	$V_{DS} = -15V, I_D = -400\mu A$
Drain Saturation Current (Pulsed)	I_{DSS}	- 1	- 5	- 2	- 9	- 4	- 16	mA	$V_{DS} = -15V, V_{GS} = 0V$

Dynamic Electrical Characteristics

Drain Source ON Resistance	$r_{ds(on)}$		2		0.8		0.4	k Ω	$V_{GS} = 0V, I_D = 0A$	f = 1 kHz
Common Source Forward Transadmittance	$ Y_{fs} $	1	4	1.5	5	2	6	mS	$V_{DS} = -15V, V_{GS} = 0V$	f = 1 kHz
Common Source Output Admittance	$ Y_{os} $		75		75		75	μS	$V_{DS} = -15V, V_{GS} = 0V$	f = 1 kHz
Common Source Input Capacitance	C_{iss}		7		7		7	pF	$V_{DS} = -15V, V_{GS} = 0V$	f = 1 MHz
Common Source Reverse Transfer Capacitance	C_{rss}		2		2		2	pF	$V_{DS} = -15V, V_{GS} = 0V$	f = 1 MHz
Equivalent Short Circuit Input Noise Voltage	\bar{e}_N		2.5		2.5		2.5	dB	$V_{DS} = -15V, V_{GS} = 0V$	f = 100 Hz, BW = 1 Hz
Noise Figure	NF		115		115		115	nV \sqrt{Hz}	$V_{DS} = -15V, V_{GS} = 0V,$ $R_G = 1M\Omega$	f = 100 Hz

TO-226AA Package

Dimensions in Inches (mm)

Pin Configuration

1 Drain, 2 Source, 3 Gate

Surface Mount

SMP5460, SMP5461, SMP5462

